- High Capacitive-Drive Capability
- Typical Delay Time of 2.6 ns (C_L = 50 pF) and Typical Power Dissipation of Less Than 9 mW Per Gate
- Center V_{CC} and GND Configuration Provides Minimum Lead Inductance in High-Current Switching Applications
- Package Options Include Plastic Small-Outline (DW) Packages and Standard Plastic (N) 300-mil DIPs

(TOP VIEW) 20 5A 5B 6Y [19 🛮 5Y 2 18 🛮 4B 6А П 3 1 4A 6B [17 16 4Y 5 V_{CC} 1A **[**] 6 15 ¶ GND 1В [14 T 3Y 7 1Y Π 8 13**∏** 3B 2A **∏** 9 12 3A 2B [] 10 11 2Y

DW OR N PACKAGE

description

This device contains six independent 2-input NAND drivers. It performs the Boolean functions $Y = \overline{A} \cdot \overline{B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

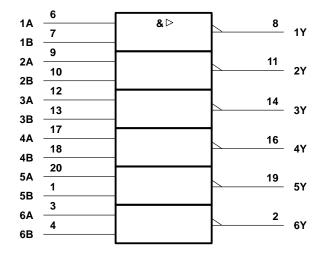
The center-pin configuration reduces lead inductance when compared to the 'AS804B. The reduced lead inductance minimizes noise generated onto either the V_{CC} or GND bus. This reduction is significant in high-current switching applications.

The SN74AS1804 is characterized for operation from 0°C to 70°C.

FUNCTION TABLE (each driver)

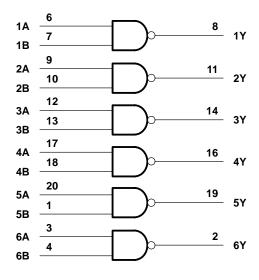
INP	UTS	OUTPUT
Α	В	Υ
Н	Н	L
L	X	Н
Х	L	Н

logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

recommended operating conditions‡

		MIN	NOM	MAX	UNIT
Vcc	Supply voltage	4.5	5	5.5	V
VIH	High-level input voltage	2			V
VIL	Low-level input voltage			0.8	V
IOH	High-level output current			-48	mA
l _{OL}	Low-level output current			48	mA
TA	Operating free-air temperature	0		70	°C

[‡] This high sink- or source-current device is not recommended for use above 40 MHz.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		MIN	TYP§	MAX	UNIT
VIK	$V_{CC} = 4.5 V,$	$I_{I} = -18 \text{ mA}$			-1.2	V
	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V},$	$I_{OH} = -2 \text{ mA}$	V _{CC} -2			
Voн	V _{CC} = 4.5 V	$I_{OH} = -3 \text{ mA}$	2.4	3.2		V
		$I_{OH} = -48 \text{ mA}$	2			
V _{OL}	$V_{CC} = 4.5 V,$	$I_{OL} = 48 \text{ mA}$		0.35	0.5	V
lį	$V_{CC} = 5.5 V,$	V _I = 7 V			0.1	mA
IIH	$V_{CC} = 5.5 V,$	V _I = 2.7 V			20	μΑ
IIL	$V_{CC} = 5.5 V,$	V _I = 0.4 V			-0.5	mA
ΙΟ [¶]	$V_{CC} = 5.5 V,$	V _O = 2.25 V	-50		-200	mA
Іссн	$V_{CC} = 5.5 V,$	V _I = 0		3.5	5	mA
lCCL	$V_{CC} = 5.5 V,$	V _I = 4.5 V		16	27	mA

[§] All typical values are at $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

switching characteristics (see Figure 1)

PARAMETER	FROM (INPUT)	10	$\label{eq:VCC} \begin{array}{l} \text{V}_{\text{CC}} = 4.5 \text{ V to } 5.5 \text{ V,} \\ \text{C}_{\text{L}} = 50 \text{ pF,} \\ \text{R}_{\text{L}} = 500 \ \Omega, \\ \text{T}_{\text{A}} = \text{MIN to MAX}^{\#} \end{array}$		UNIT
			MIN	MAX	
^t PLH	A or B	V	1	4	
[†] PHL		,	1	4	ns

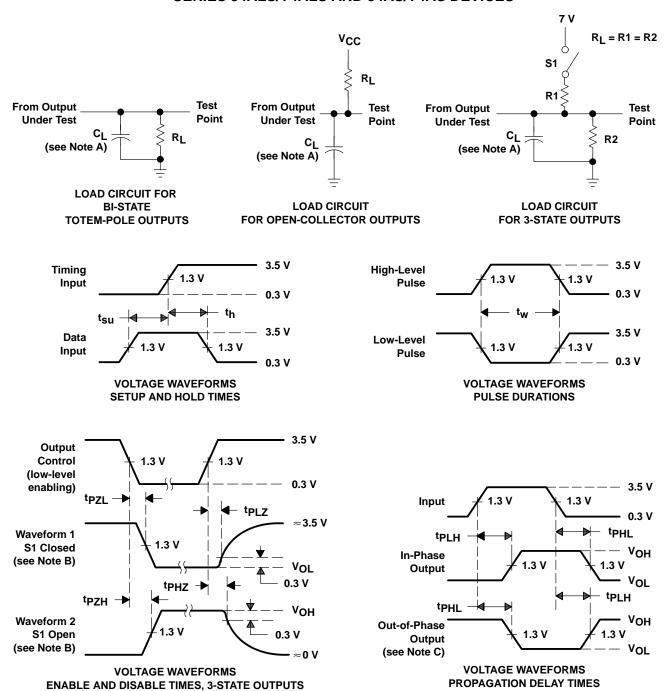
[#] For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.



[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

The output conditions have been chosen to produce a current that closely approximates one half of the true short-circuit output current, IOS.

PARAMETER MEASUREMENT INFORMATION SERIES 54ALS/74ALS AND 54AS/74AS DEVICES



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. When measuring propagation delay items of 3-state outputs, switch S1 is open.
- D. All input pulses have the following characteristics: PRR \leq 1 MHz, $t_f = t_f = 2$ ns, duty cycle = 50%.
- E. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms



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